



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Attorney Docket No. 016907/0935

In re reissue of U.S. Patent No. 5,552,949

Susumu HASHIMOTO et al.

Serial No.: 09/785,458

Group Art Unit: 2652

Filing Date: February 20, 2001

Examiner: B. Miller

For: MAGNETORESISTANCE EFFECT ELEMENT WITH IMPROVED
ANTIFERROMAGNETIC LAYER

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SUPPLEMENTAL AMENDMENT AND REPLY

Commissioner for Patents
Washington, D.C. 20231

Sir:

This Supplemental Amendment supercedes the Amendment filed December 11, 2001 and is provided in reply to the Office Action mailed September 11, 2001 and to the interview held on December 13, 2001. Please amend the above-identified application as follows:

IN THE CLAIMS:

Cancel claims 41 and 42.

Please amend the claims as follows:

11. A magnetoresistance effect element comprising:

a spin valve film comprising a first ferromagnetic layer, a nonmagnetic layer, a second ferromagnetic layer, and an antiferromagnetic layer, wherein the nonmagnetic layer is provided between the first and second ferromagnetic layers, and the antiferromagnetic layer is provided adjacent to the first or second ferromagnetic layer, the antiferromagnetic layer comprising an alloy of NM, where N comprises Pt and M comprises Mn.

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